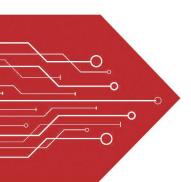
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet



Features

Ideal for printed circuit board

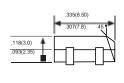
Reliable low cost construction utilizing molded plastic technique

High temperature soldering guaranteed: 260°/10 seconds at 5

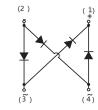
lbs., (2.3kg) tension

Small size, simple installation High surge current capability

.047(1.20) .035(0.9)



.014(0.35) .008(0.20) .060(1.53) .002(0.20)



Dimensions in inches and (millimeters)

Mechanical Data

Case: JEDEC DBS Molded plastic body

Terminals: Solder plated, solderable per MIL-STD-750, Method 2026

Polarity: Polarity symbol marking on body

Mounting Position: Any

Weight: 0.02 ounce, 0.4 grams

REEL SPECIFICATION

P/N	PKG	QTY
DB151S-DB157S	DBS	1500

Maximum Ratings And Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwisespecified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter		DB151S	DB152S	DB153S	DB154S	DB155S	DB156S	DB157S	UNITS
Marking Code	SYMBOLS								
Maximum repetitive peak reverse voltage	VRRM	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	VDC	50	100	200	400	600	800	1000	V
Maximum average forward rectified current at T _C =40°C		1.5						Α	
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)		50						А	
Maximum instantaneous forward voltage drop per leg at 1.5A		1.1					V		
Maximum DC reverse current T _A =25°C at rated DC blocking voltage T _A =100°C	lR	10 500					μA μA		
Operating temperature range		-55 to +150						°C	
storage temperature range	Тѕтс			-!	55 to +15	0			°C

NOTES:DBS for surface mount package.



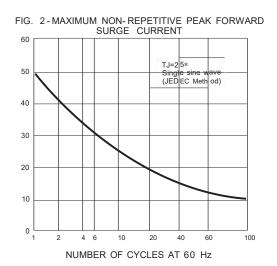




AVERAGE FORWARD CURRENT(A)

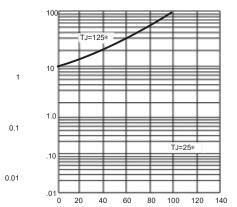
FIG. 1- MAXIMUN DERATING CURVE FOR OUTPUT RECTIFIED CURRENT 0.6 '(1.5mm 2.0 Opper Pa uls .51"x. 51" (13mmx13 mm) 1.5 1.0 0.5 0 20 140 150 AMBIENT TEMPERATURE, C

PEAK FORWARD CURRENT.(A)



INSTANTANEOUS REVERSE CURRENT(*A)

FIG. 3-TYPICAL REVERSE CHARACTERISTICS PER BRIDGE ELEMENT



PERCENT OF RATED PEAK REVERSE VOLTAGE.(%)

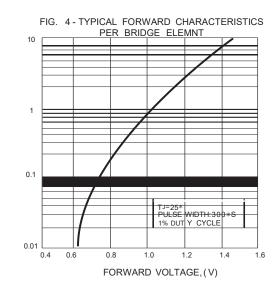
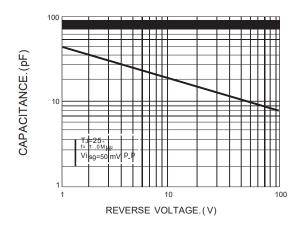


FIG. 3-TYPICAL JUNCTION CAPACITANCE PER BRIDGE ELEMENT

INSTANTANEOUS REVERSE CURRENT.(A)







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